

Preliminary datasheet

62 mm C-Series module with CoolSiC™ Trench MOSFET

Features

- Electrical features
 - $V_{DS} = 1200\text{ V}$
 - $I_{DN} = 560\text{ A} / I_{DRM} = 1120\text{ A}$
 - High current density
 - Low switching losses
- Mechanical features
 - 4 kV AC 1 min insulation

Potential applications

- UPS systems
- Solar applications
- DC/DC converter
- High-frequency switching application
- Energy storage systems
- DC charger for EV

Product validation

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

Description

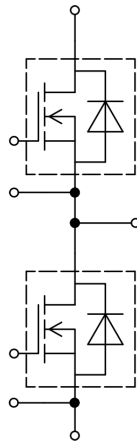


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1 Package

Table 1 Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	V_{ISOL}	RMS, $f = 50 \text{ Hz}$, $t = 60 \text{ s}$	4.0	kV
Material of module baseplate			Cu	
Internal isolation		basic insulation (class 1, IEC 61140)	Al_2O_3	
Creepage distance	d_{Creep}	terminal to heatsink	29.0	mm
Creepage distance	d_{Creep}	terminal to terminal	23.0	mm
Clearance	d_{Clear}	terminal to heatsink	23.0	mm
Clearance	d_{Clear}	terminal to terminal	11.0	mm
Comparative tracking index	CTI		> 400	
Relative thermal index (electrical)	RTI	housing	140	°C

Table 2 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Stray inductance module	L_{sCE}			20		nH
Module lead resistance, terminals - chip	$R_{CC'+EE'}$	$T_C = 25 \text{ °C}$, per switch		0.465		mΩ
Storage temperature	T_{stg}		-40		125	°C
Mounting torque for module mounting	M	- Mounting according to valid application note	M6, Screw	3	6	Nm
Terminal connection torque	M	- Mounting according to valid application note	M6, Screw	2.5	5	Nm
Weight	G			340		g

2 MOSFET

Table 3 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Drain-source voltage	V_{DSS}	$T_{vj} = 25 \text{ °C}$	1200	V
Implemented drain current	I_{DN}		560	A
Continuous DC drain current	I_{DDC}	$T_{vj} = 175 \text{ °C}$, $V_{GS} = 18 \text{ V}$ $T_C = 115 \text{ °C}$	390	A
Repetitive peak drain current	I_{DRM}	verified by design, t_p limited by T_{vjmax}	1120	A

(table continues...)

Table 3 (continued) Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Gate-source voltage, max. transient voltage	V_{GS}	$D < 0.01$	-10/23	V
Gate-source voltage, max. static voltage	V_{GS}		-7/20	V

Table 4 Recommended values

Parameter	Symbol	Note or test condition	Values	Unit
On-state gate voltage	$V_{GS(on)}$		15...18	V
Off-state gate voltage	$V_{GS(off)}$		-5...0	V

Table 5 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Drain-source on-resistance	$R_{DS(on)}$	$I_D = 560 \text{ A}$	$V_{GS} = 18 \text{ V}, T_{vj} = 25 \text{ °C}$		1.47		mΩ
			$V_{GS} = 18 \text{ V}, T_{vj} = 125 \text{ °C}$		2.38		
			$V_{GS} = 18 \text{ V}, T_{vj} = 175 \text{ °C}$		3.16		
			$V_{GS} = 15 \text{ V}, T_{vj} = 25 \text{ °C}$		1.77		
Gate threshold voltage	$V_{GS(th)}$	$I_D = 224 \text{ mA}, V_{DS} = V_{GS}, T_{vj} = 25 \text{ °C},$ (tested after 1ms pulse at $V_{GS} = +20 \text{ V}$)		3.45	4.3	5.15	V
Total gate charge	Q_G	$V_{DD} = 800 \text{ V}, V_{GS} = -3/18 \text{ V}$			1.6		μC
Internal gate resistor	R_{Gint}	$T_{vj} = 25 \text{ °C}$			0.9		Ω
Input capacitance	C_{ISS}	$f = 100 \text{ kHz}, V_{DS} = 800 \text{ V}, V_{GS} = 0 \text{ V}$	$T_{vj} = 25 \text{ °C}$		48.4		nF
Output capacitance	C_{OSS}	$f = 100 \text{ kHz}, V_{DS} = 800 \text{ V}, V_{GS} = 0 \text{ V}$	$T_{vj} = 25 \text{ °C}$		2.4		nF
Reverse transfer capacitance	C_{rss}	$f = 100 \text{ kHz}, V_{DS} = 800 \text{ V}, V_{GS} = 0 \text{ V}$	$T_{vj} = 25 \text{ °C}$		0.158		nF
C_{OSS} stored energy	E_{OSS}	$V_{DS} = 800 \text{ V}, V_{GS} = -3/18 \text{ V}, T_{vj} = 25 \text{ °C}$			945		μJ
Drain-source leakage current	I_{DSS}	$V_{DS} = 1200 \text{ V}, V_{GS} = -3 \text{ V}$	$T_{vj} = 25 \text{ °C}$		0.32	660	μA
Gate-source leakage current	I_{GSS}	$V_{DS} = 0 \text{ V}, T_{vj} = 25 \text{ °C}$	$V_{GS} = 20 \text{ V}$			400	nA

(table continues...)

Table 5 (continued) **Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Turn-on delay time (inductive load)	$t_{d\ on}$	$I_D = 560\ A, R_{Gon} = 4.3\ \Omega,$ $V_{DD} = 600\ V, V_{GS} = -3/18\ V$	$T_{vj} = 25\ ^\circ C$	166		ns
			$T_{vj} = 125\ ^\circ C$	155		
			$T_{vj} = 175\ ^\circ C$	150		
Rise time (inductive load)	t_r	$I_D = 560\ A, R_{Gon} = 4.3\ \Omega,$ $V_{DD} = 600\ V, V_{GS} = -3/18\ V$	$T_{vj} = 25\ ^\circ C$	172		ns
			$T_{vj} = 125\ ^\circ C$	152		
			$T_{vj} = 175\ ^\circ C$	155		
Turn-off delay time (inductive load)	$t_{d\ off}$	$I_D = 560\ A, R_{Goff} = 1.8\ \Omega,$ $V_{DD} = 600\ V, V_{GS} = -3/18\ V$	$T_{vj} = 25\ ^\circ C$	180		ns
			$T_{vj} = 125\ ^\circ C$	196		
			$T_{vj} = 175\ ^\circ C$	204		
Fall time (inductive load)	t_f	$I_D = 560\ A, R_{Goff} = 1.8\ \Omega,$ $V_{DD} = 600\ V, V_{GS} = -3/18\ V$	$T_{vj} = 25\ ^\circ C$	43		ns
			$T_{vj} = 125\ ^\circ C$	44		
			$T_{vj} = 175\ ^\circ C$	45		
Turn-on energy loss per pulse	E_{on}	$I_D = 560\ A, V_{DD} = 600\ V,$ $L_\sigma = 10\ nH, V_{GS} = -3/18\ V,$ $R_{Gon} = 4.3\ \Omega, di/dt = 5.9$ $kA/\mu s (T_{vj} = 175\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$	23.9		mJ
			$T_{vj} = 125\ ^\circ C$	23.1		
			$T_{vj} = 175\ ^\circ C$	23.3		
Turn-off energy loss per pulse	E_{off}	$I_D = 560\ A, V_{DD} = 600\ V,$ $L_\sigma = 10\ nH, V_{GS} = -3/18\ V,$ $R_{Goff} = 1.8\ \Omega, dv/dt = 10.7$ $kV/\mu s (T_{vj} = 175\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$	15		mJ
			$T_{vj} = 125\ ^\circ C$	16.2		
			$T_{vj} = 175\ ^\circ C$	16.7		
Thermal resistance, junction to case	R_{thJC}	per MOSFET			0.0830	K/W
Thermal resistance, case to heat sink	R_{thCH}	per MOSFET, $\lambda_{grease} = 1\ W/(m \cdot K)$		0.0200		K/W
Temperature under switching conditions	$T_{vj\ op}$		-40		175	$^\circ C$

Note: The selection of positive and negative gate-source voltages impacts losses and the long-term behavior of the MOSFET and body diode. The design guidelines described in Application Notes AN 2018-09 and AN 2021-13 must be considered to ensure sound operation of the device over the planned lifetime.

$T_{vj,op} > 150\ ^\circ C$ is allowed for operation at overload conditions for MOSFET and body diode. For detailed specifications, please refer to AN 2021-13.

3 Body diode (MOSFET)

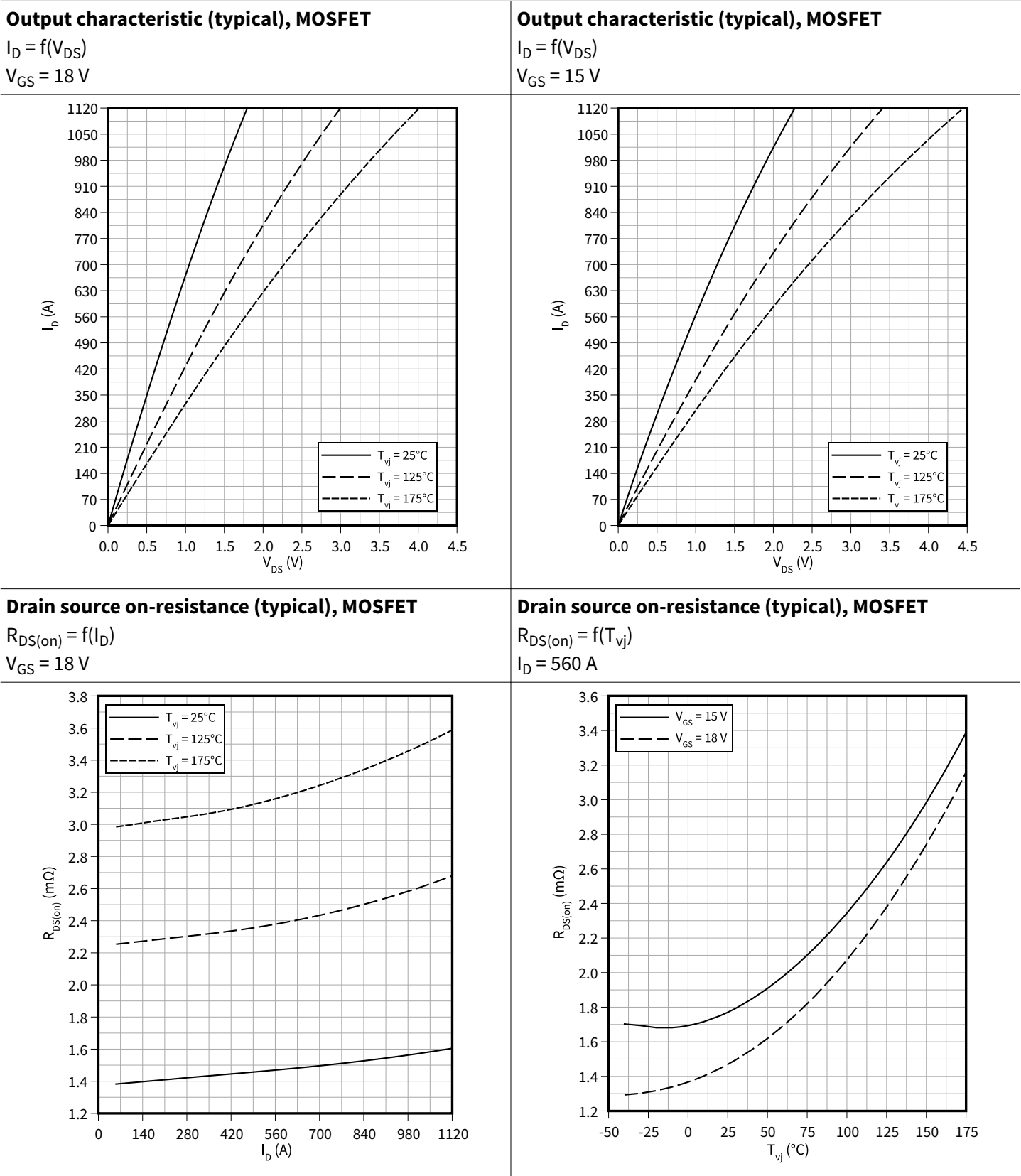
Table 6 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
DC body diode forward current	I_{SD}	$T_{vj} = 175\text{ °C}$, $V_{GS} = -3\text{ V}$	$T_C = 115\text{ °C}$	185	A

Table 7 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Forward voltage	V_{SD}	$I_{SD} = 560\text{ A}$, $V_{GS} = -3\text{ V}$	$T_{vj} = 25\text{ °C}$		4.22	5.59	V
			$T_{vj} = 125\text{ °C}$		3.95		
			$T_{vj} = 175\text{ °C}$		3.85		

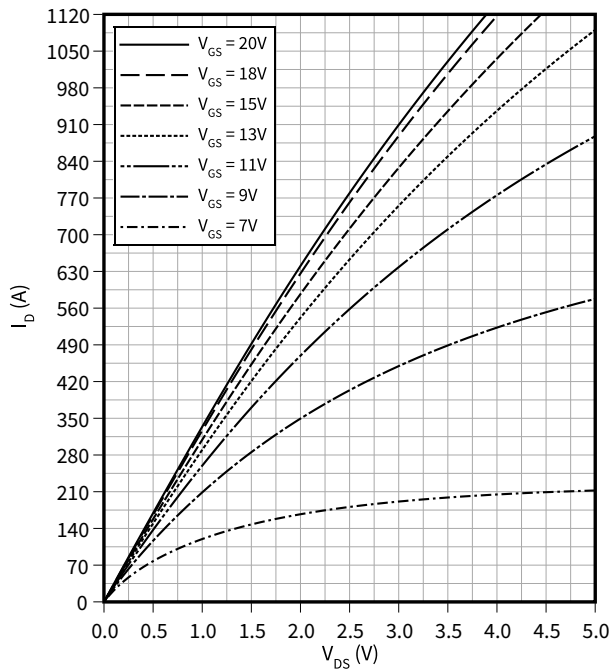
4 Characteristics diagrams



4 Characteristics diagrams

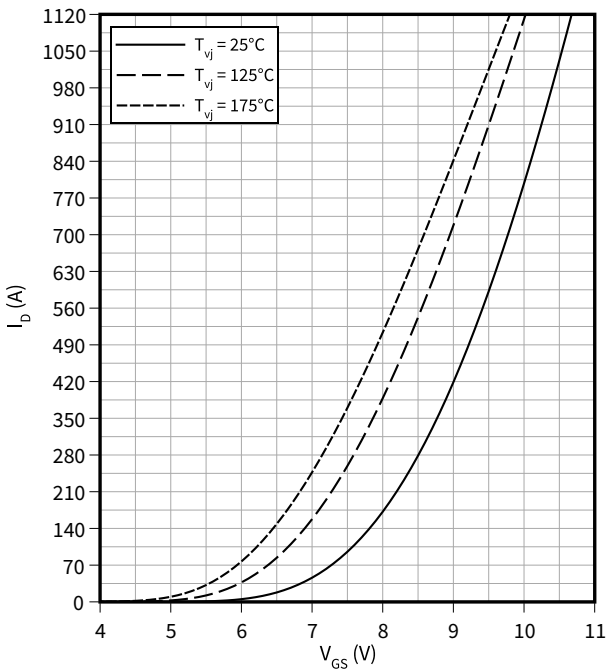
Output characteristic field (typical), MOSFET

$I_D = f(V_{DS})$
 $T_{vj} = 175\text{ °C}$



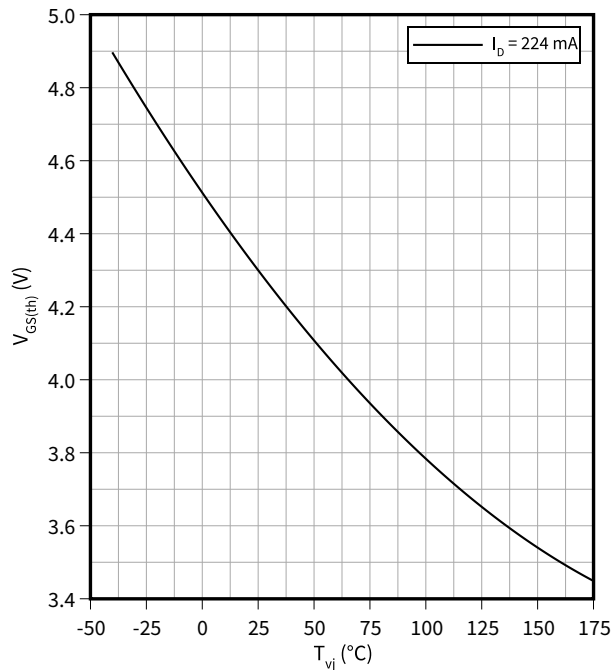
Transfer characteristic (typical), MOSFET

$I_D = f(V_{GS})$
 $V_{DS} = 20\text{ V}$



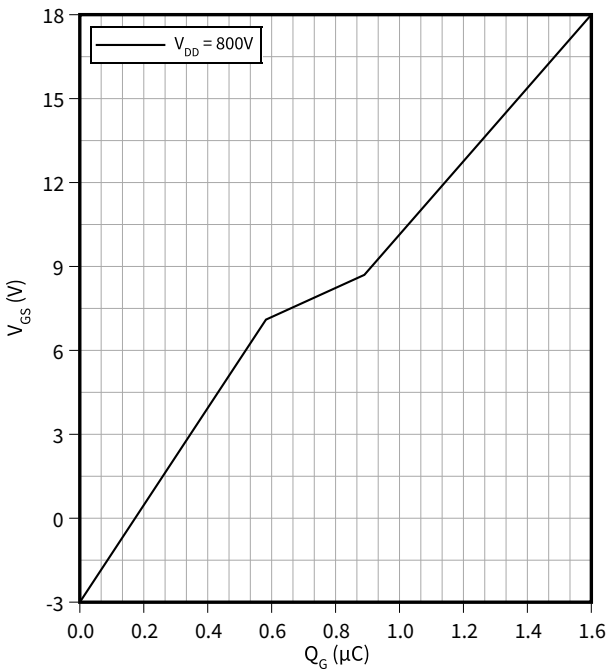
Gate-source threshold voltage (typical), MOSFET

$V_{GS(th)} = f(T_{vj})$
 $V_{GS} = V_{DS}$



Gate charge characteristic (typical), MOSFET

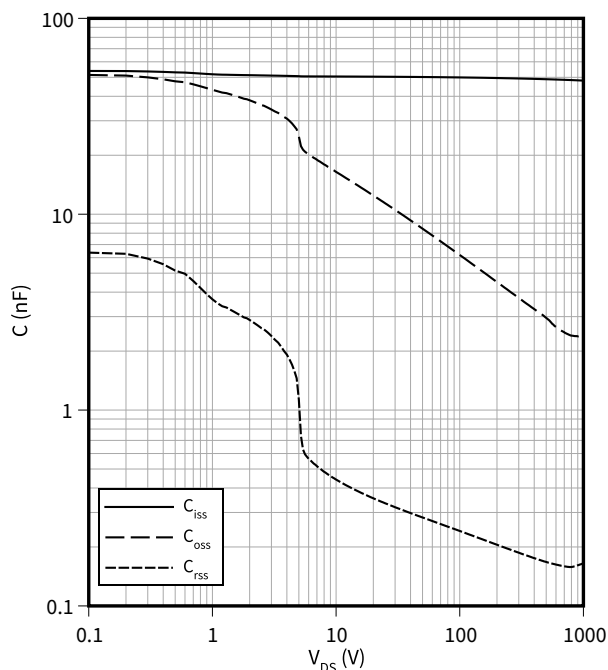
$V_{GS} = f(Q_G)$
 $I_D = 560\text{ A}, T_{vj} = 25\text{ °C}$



Capacity characteristic (typical), MOSFET

$$C = f(V_{DS})$$

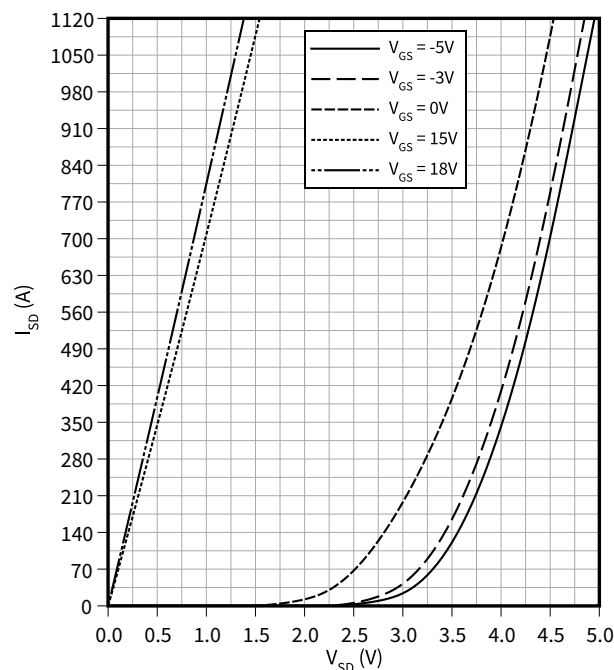
$T_{vj} = 25^\circ\text{C}$, $V_{GS} = 0\text{ V}$, $f = 100\text{ kHz}$



Forward characteristic body diode (typical), MOSFET

$$I_{SD} = f(V_{SD})$$

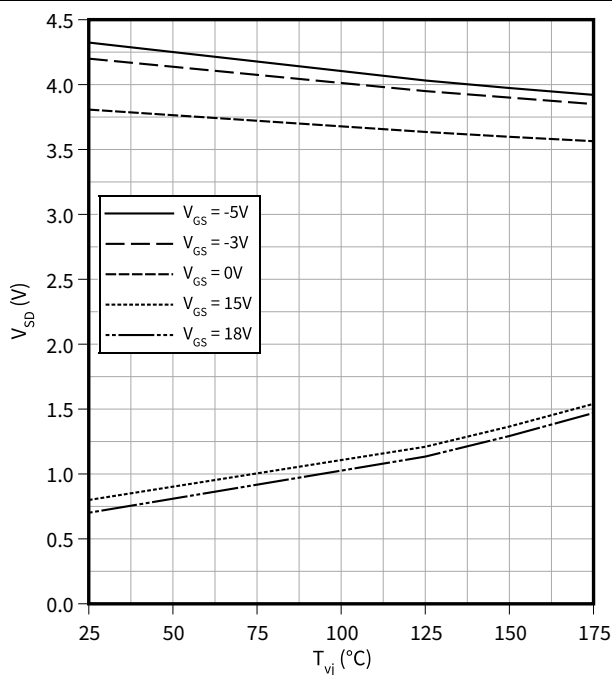
$T_{vj} = 25^\circ\text{C}$



Forward voltage of body diode (typical), MOSFET

$$V_{SD} = f(T_{vj})$$

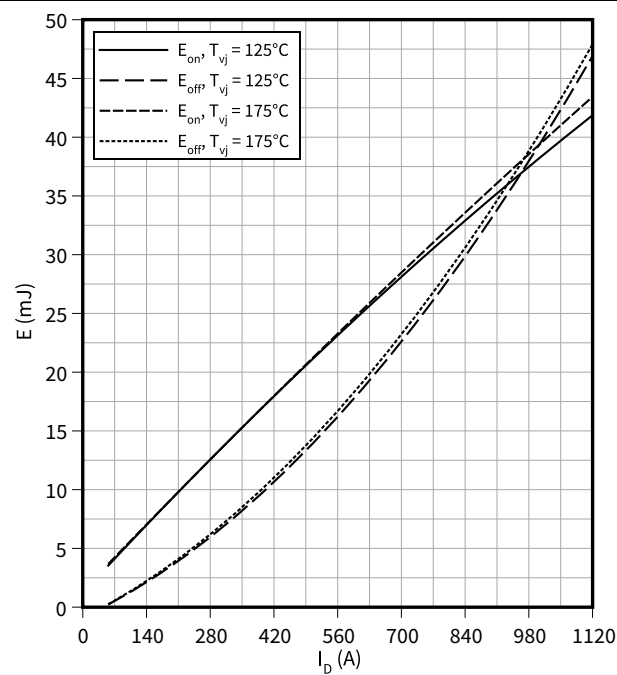
$I_{SD} = 560\text{ A}$



Switching losses (typical), MOSFET

$$E = f(I_D)$$

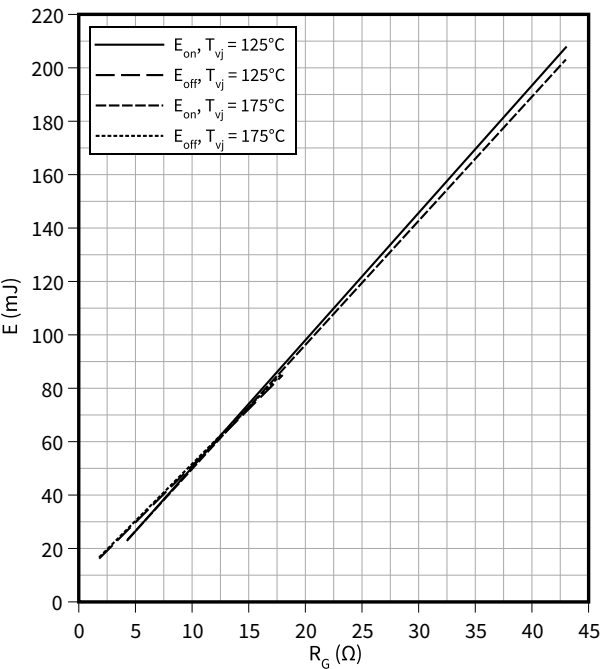
$R_{Goff} = 1.8\ \Omega$, $R_{Gon} = 4.3\ \Omega$, $V_{DD} = 600\text{ V}$, $V_{GS} = -3/18\text{ V}$



4 Characteristics diagrams

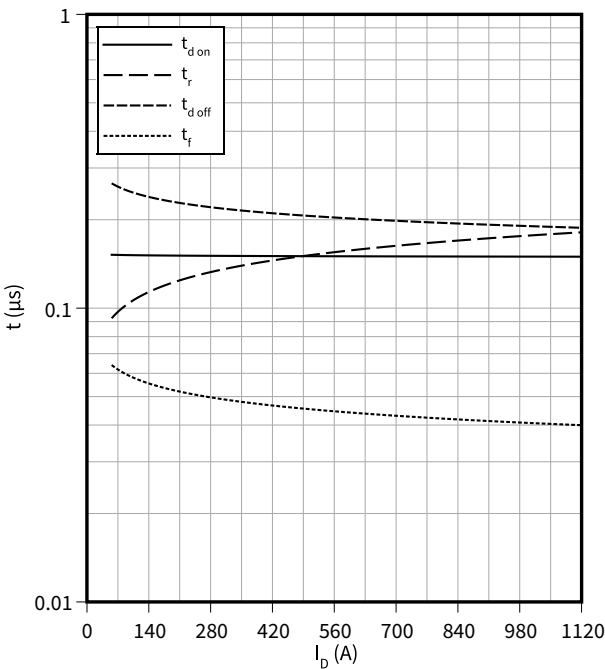
Switching losses (typical), MOSFET

$E = f(R_G)$
 $V_{DD} = 600\text{ V}$, $I_D = 560\text{ A}$, $V_{GS} = -3/18\text{ V}$



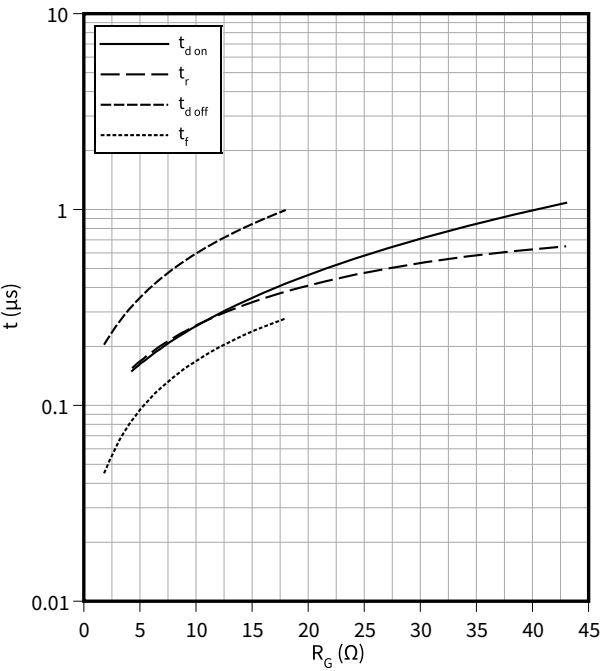
Switching times (typical), MOSFET

$t = f(I_D)$
 $R_{Goff} = 1.8\text{ }\Omega$, $R_{Gon} = 4.3\text{ }\Omega$, $V_{DD} = 600\text{ V}$, $T_{vj} = 175\text{ }^\circ\text{C}$, $V_{GS} = -3/18\text{ V}$



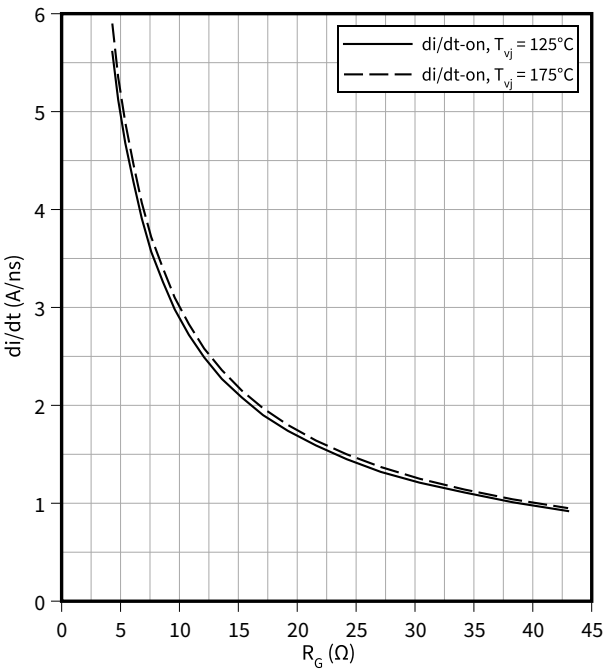
Switching times (typical), MOSFET

$t = f(R_G)$
 $V_{DD} = 600\text{ V}$, $I_D = 560\text{ A}$, $T_{vj} = 175\text{ }^\circ\text{C}$, $V_{GS} = -3/18\text{ V}$



Current slope (typical), MOSFET

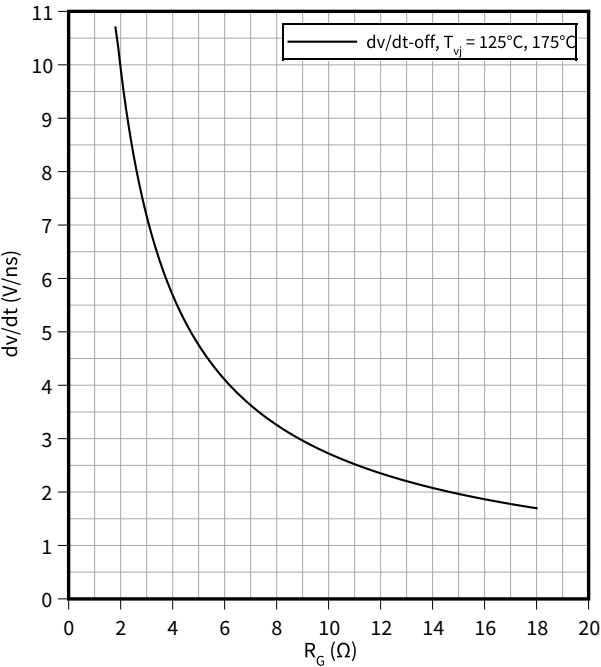
$di/dt = f(R_G)$
 $V_{DD} = 600\text{ V}$, $I_D = 560\text{ A}$, $V_{GS} = -3/18\text{ V}$



4 Characteristics diagrams

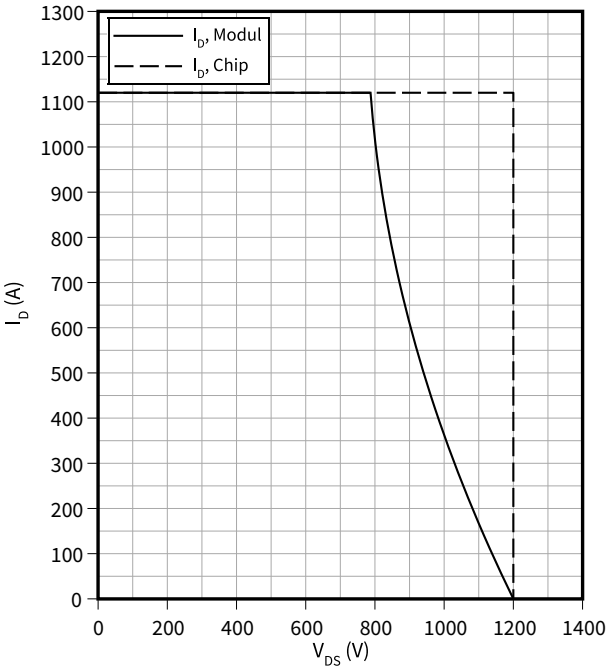
Voltage slope (typical), MOSFET

$dv/dt = f(R_G)$
 $V_{DD} = 600\text{ V}$, $I_D = 560\text{ A}$, $V_{GS} = -3/18\text{ V}$



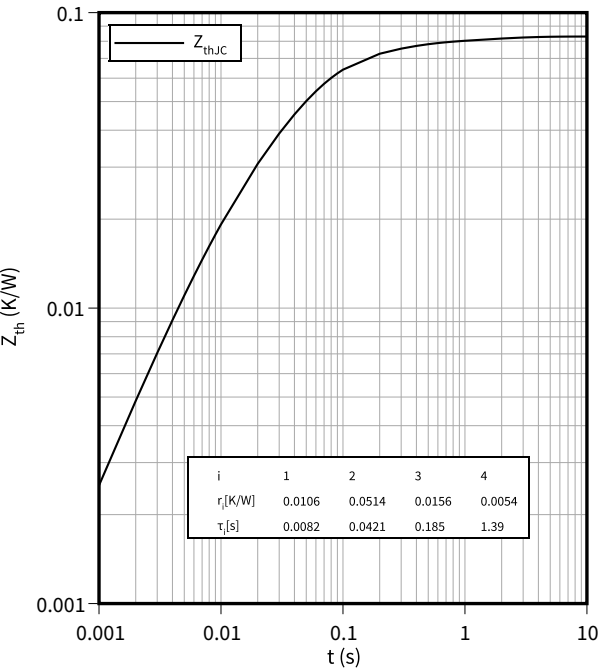
Reverse bias safe operating area (RBSOA), MOSFET

$I_D = f(V_{DS})$
 $R_{Goff} = 1.8\text{ }\Omega$, $T_{vj} = 175\text{ }^\circ\text{C}$, $V_{GS} = -3/18\text{ V}$



Transient thermal impedance, MOSFET

$Z_{th} = f(t)$



5 **Circuit diagram**

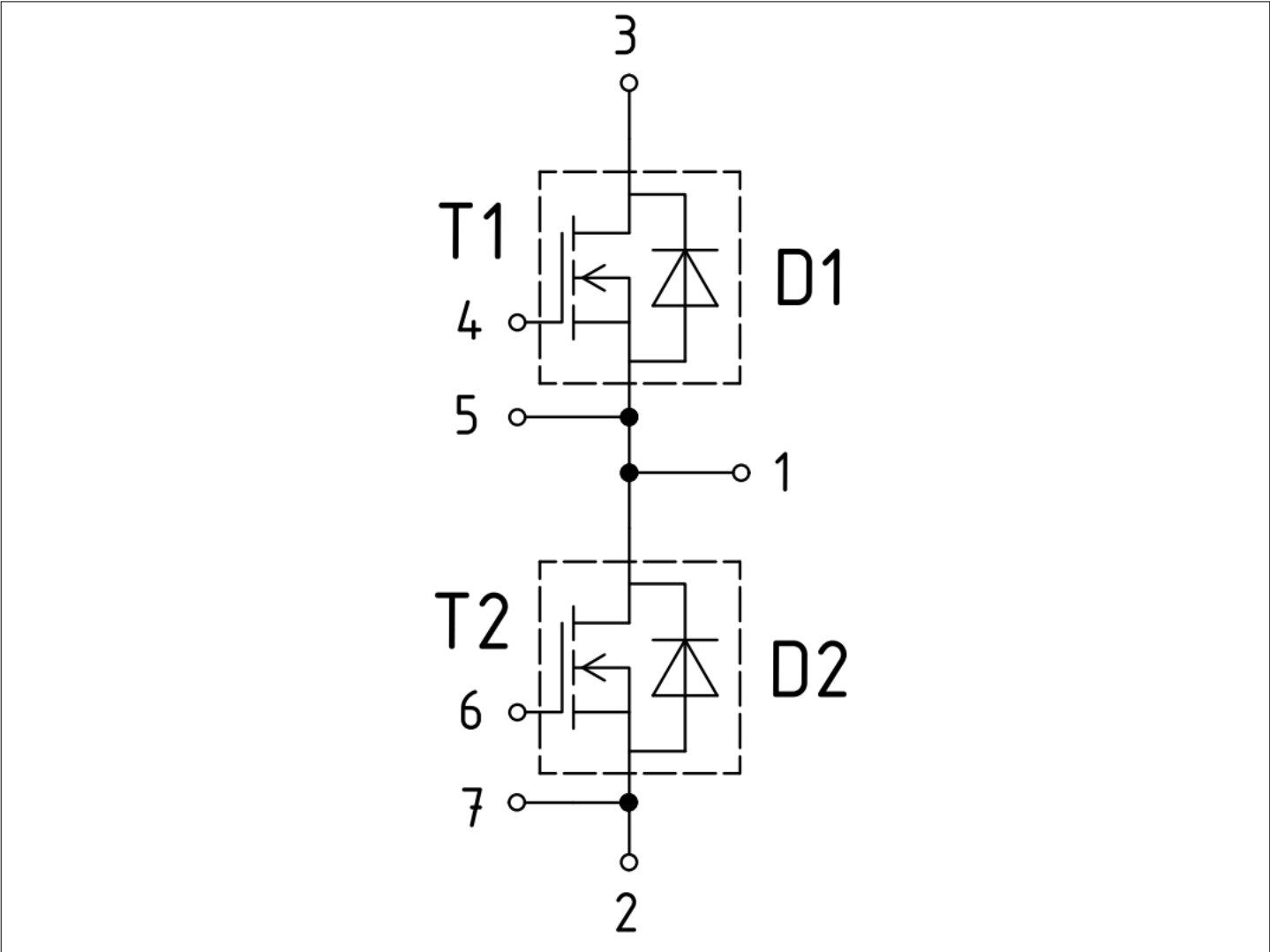


Figure 1

6 Package outlines

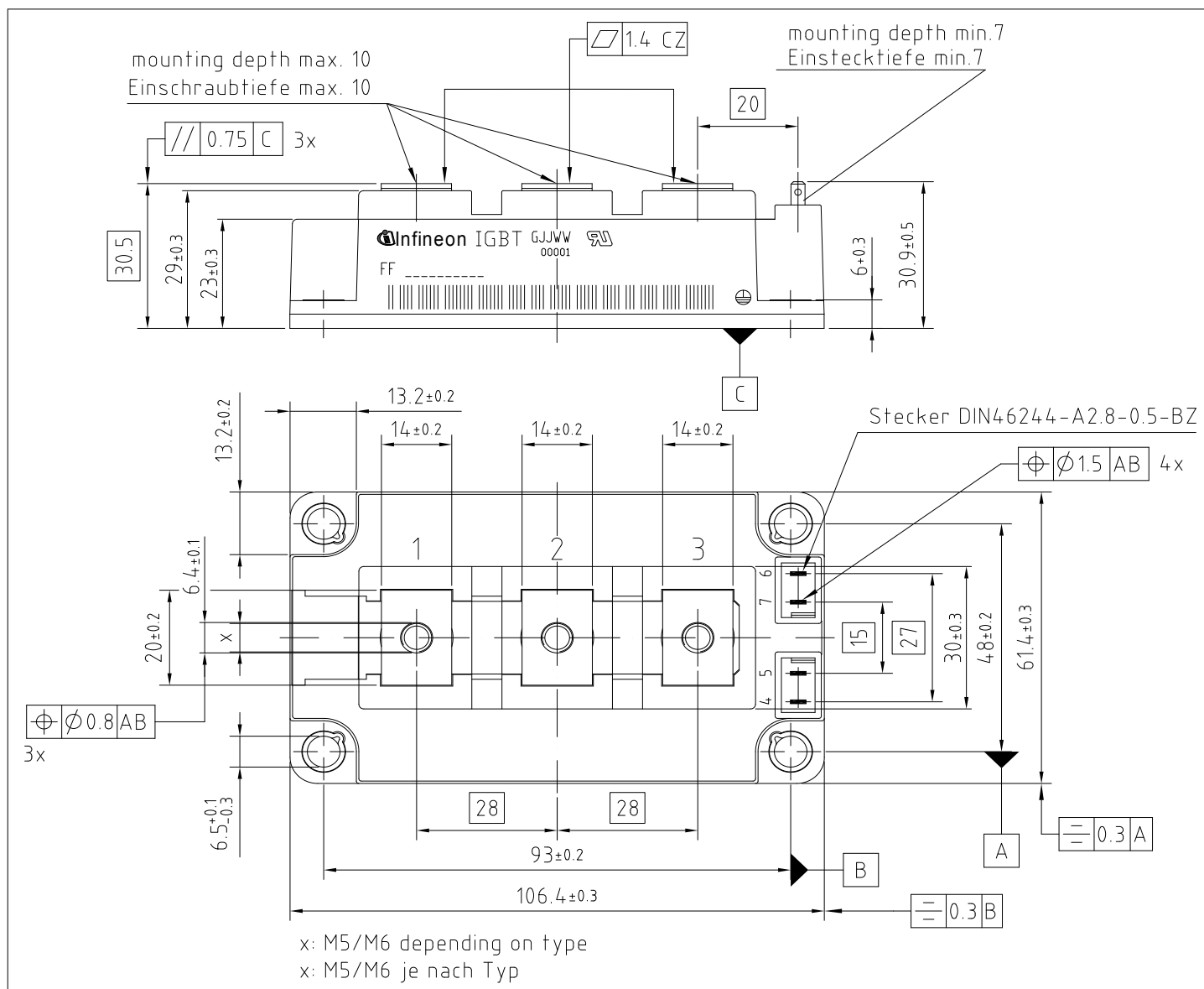


Figure 2

7 Module label code



Module label code			
Code format	Data Matrix		Barcode Code128
Encoding	ASCII text		Code Set A
Symbol size	16x16		23 digits
Standard	IEC24720 and IEC16022		IEC8859-1
Code content	<i>Content</i>	<i>Digit</i>	<i>Example</i>
	Module serial number	1 – 5	71549
	Module material number	6 - 11	142846
	Production order number	12 - 19	55054991
	Date code (production year)	20 – 21	15
	Date code (production week)	22 – 23	30
Example	<div> 71549142846550549911530</div> <div> 71549142846550549911530</div>		

Figure 3

Revision history

Document revision	Date of release	Description of changes
0.10	2023-01-17	Initial version
0.20	2023-02-21	Preliminary datasheet

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